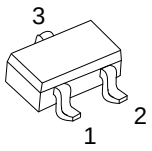
02P35Z

POWER MOSFET

200mA, 350V P-CHANNEL POWER MOSFET



SOT-23
(EIAJ SC-59)

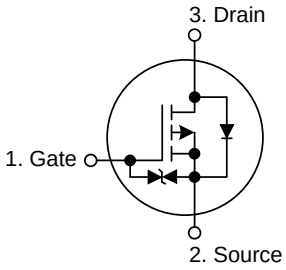
■ DESCRIPTION

The UTC **02P35Z** is a silicon P-channel MOSFET, it uses UTC's advanced technology to provide the customers with a minimum on state resistance, high switching speed and low gate charge.

■ FEATURES

* $R_{DS(ON)}$ ≤ 15Ω @ V_{GS}=-10V, I_D=-0.1A
  $R_{DS(ON)}$ ≤ 16.5Ω @ V_{GS}=-4.5V, I_D=-0.1A
* High switching speed
* Low input capacitance

■ SYMBOL



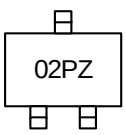
■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
02P35ZL-AE3-R	02P35ZG-AE3-R	SOT-23	G	S	D	Tape Reel

Note: Pin Assignment: G: Gate S: Source D: Drain

02P35ZG-AE3-R (1)Packing Type (2)Package Type (3)Green Package	(1) R: Tape Reel (2) AE3: SOT-23 (3) G: Halogen Free and Lead Free, L: Lead Free

■ MARKING



■ ABSOLUTE MAXIMUM RATING (T_C=25°C unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	-350	V
Gate-Source Voltage		V_{GSS}	±20	V
Drain Current	DC	I_D	-0.2	A
	Pulsed (Note 2)	I_{DM}	-0.4	A
Power Dissipation		P_D	0.3	W
Junction Temperature		T_J	+150	°C
Storage Temperature Range		T_{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating : Pulse width limited by maximum junction temperature.

■ THERMAL DATA

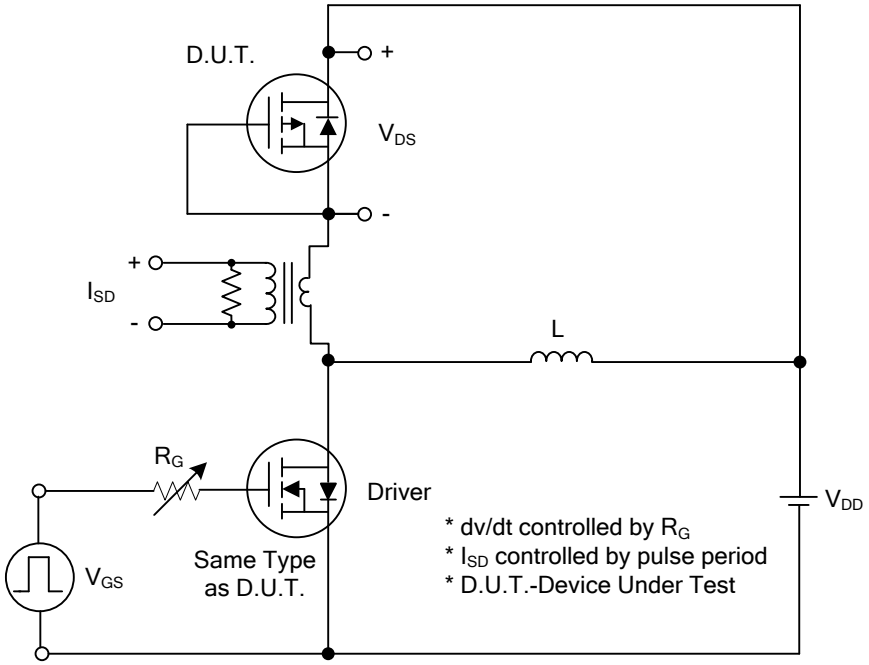
PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	350	°C/W

■ ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise specified)

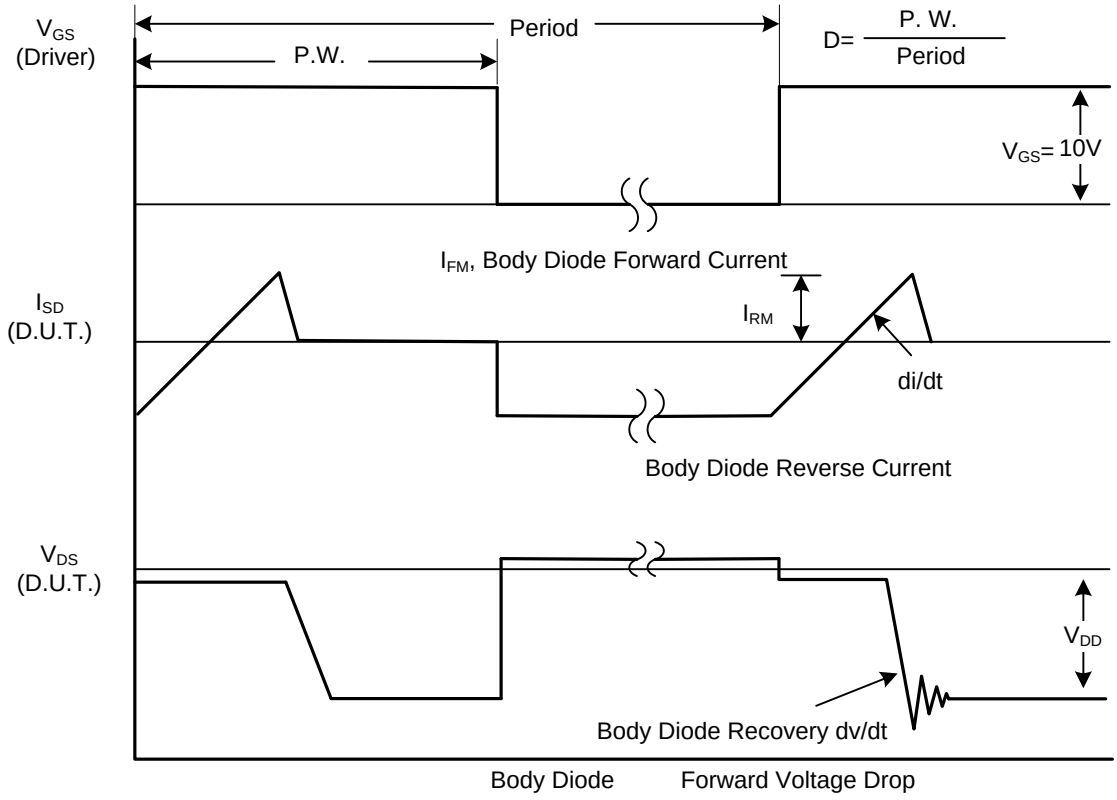
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	V_{GS}=0V, I_D=-250μA	-350			V
Drain-Source Leakage Current		I_{DSS}	V_{DS}=-350V, V_{GS}=0V			-10	μA
Gate-Source Leakage Current	Forward	I_{GSS}	V_{GS}=+20V, V_{DS}=0V			+10	μA
	Reverse		V_{GS}=-20V, V_{DS}=0V			-10	μA
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	V_{DS}= V_{GS}, I_D=-250μA	-1.0		-2.5	V
Static Drain-Source On-State Resistance		$R_{DS(ON)}$	V_{GS} =-10V, I_D =-0.1A			15	Ω
			V_{GS} =-4.5V, I_D =-0.1A			16.5	Ω
DYNAMIC PARAMETERS							
Input Capacitance		C_{ISS}	V_{GS}=0V, V_{DS}=-25V, f=1.0MHz		77		pF
Output Capacitance		C_{OSS}			17.7		pF
Reverse Transfer Capacitance		C_{RSS}			4		pF
SWITCHING PARAMETERS							
Total Gate Charge		Q_G	V_{DS}=-280V, V_{GS}=-10V, I_D=-200mA , I_G=-1mA (Note 1, 2)		8.4		nC
Gate to Source Charge		Q_{GS}			1.92		nC
Gate to Drain Charge		Q_{GD}			0.9		nC
Turn-ON Delay Time		$t_{D(ON)}$	V_{DD}=-100V, V_{GS}=-10V, I_D=-200mA, R_G=25Ω (Note 1, 2)		3.2		ns
Rise Time		t_R			17.3		ns
Turn-OFF Delay Time		$t_{D(OFF)}$			22.4		ns
Fall-Time		t_F			43.9		ns
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Continuous Drain-Source Diode Forward Current		I_S				-1	A
Maximum Pulsed Drain-Source Diode Forward Current		I_{SM}				-2	A
Diode Forward Voltage		V_{SD}	I_F=-0.2A, V_{GS}=0V			-1.4	V

Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%.
2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

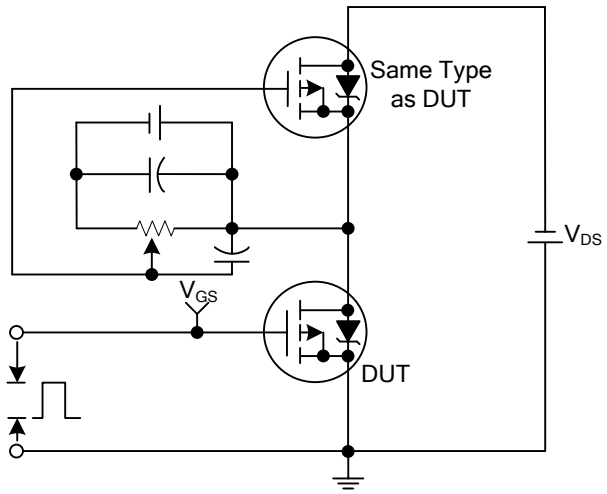


Peak Diode Recovery dv/dt Test Circuit

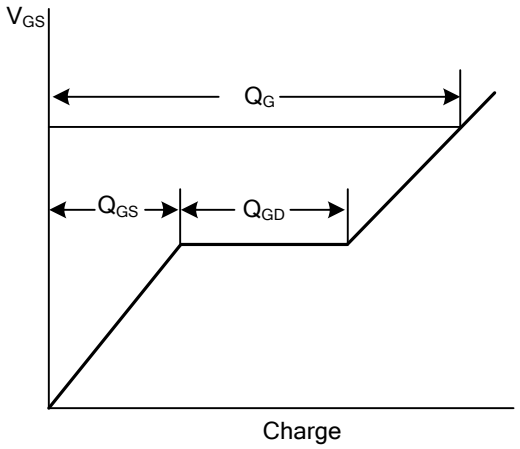


Peak Diode Recovery dv/dt Waveforms

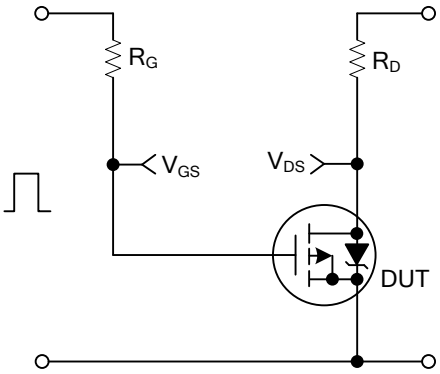
■ TEST CIRCUITS AND WAVEFORMS



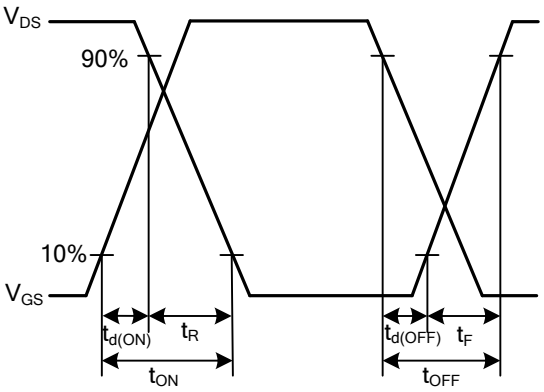
Gate Charge Test Circuit



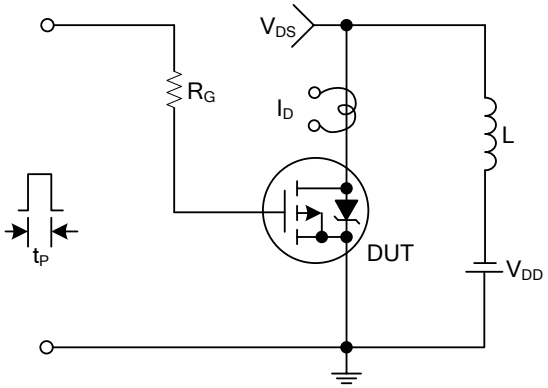
Gate Charge Waveforms



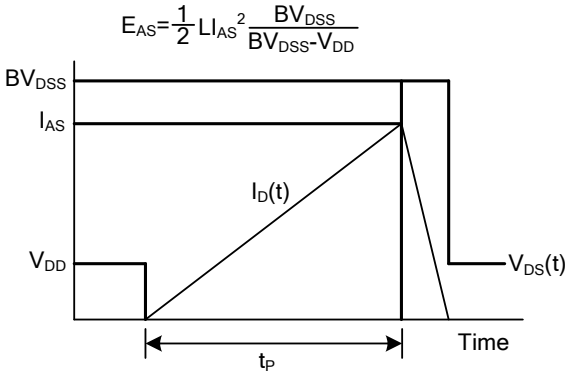
Resistive Switching Test Circuit



Resistive Switching Waveforms



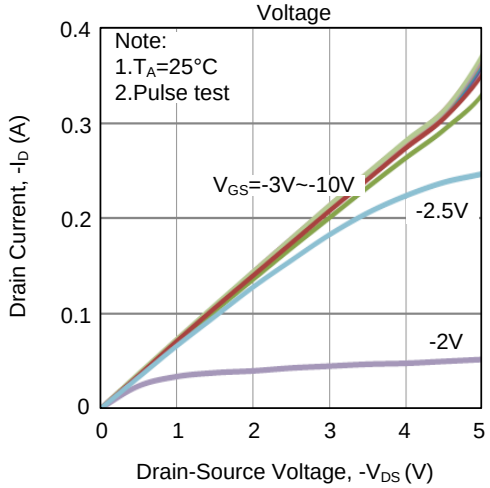
Unclamped Inductive Switching Test Circuit



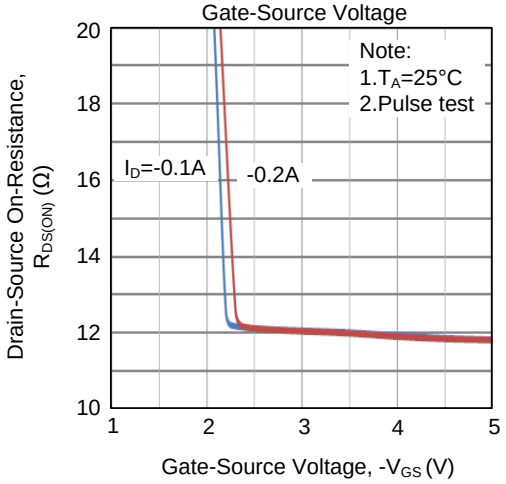
Unclamped Inductive Switching Waveforms

■ TYPICAL CHARACTERISTICS

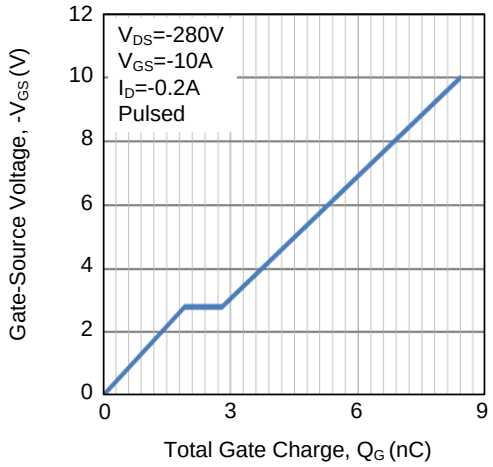
Drain Current vs. Drain-Source Voltage



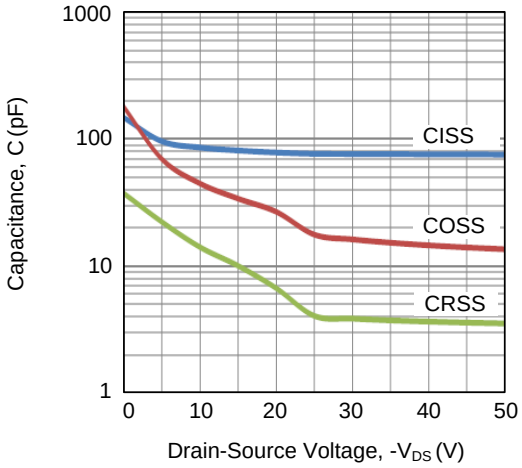
Drain-Source On-Resistance vs. Gate-Source Voltage



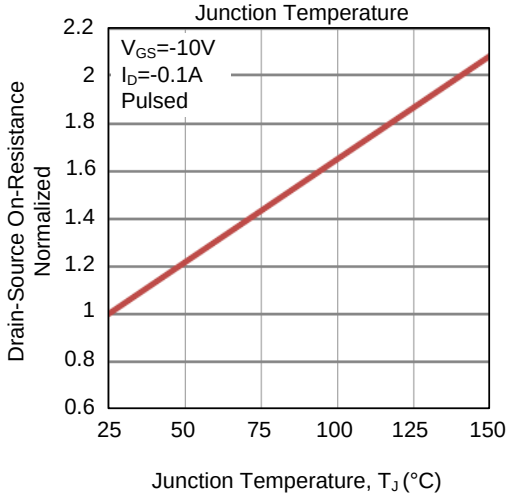
Gate Charge Characteristics



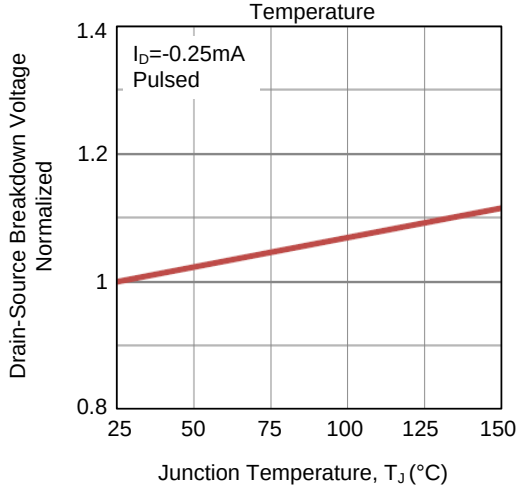
Capacitance Characteristics



Drain-Source On-Resistance vs. Junction Temperature

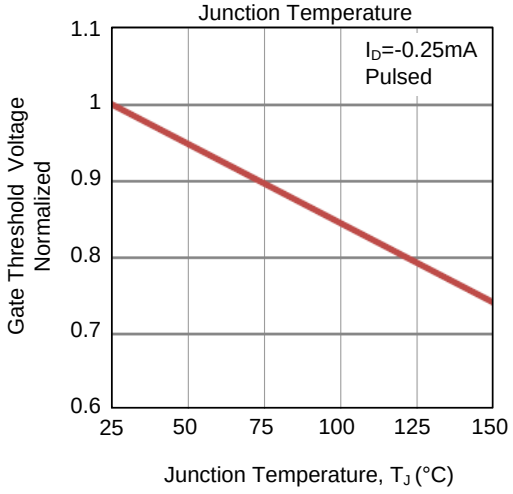


Breakdown Voltage vs. Junction Temperature

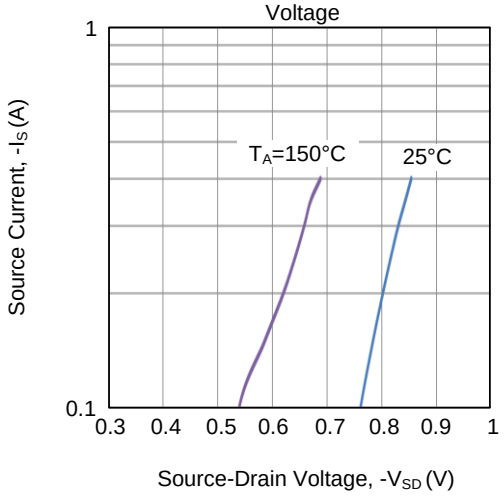


■ TYPICAL CHARACTERISTICS (Cont.)

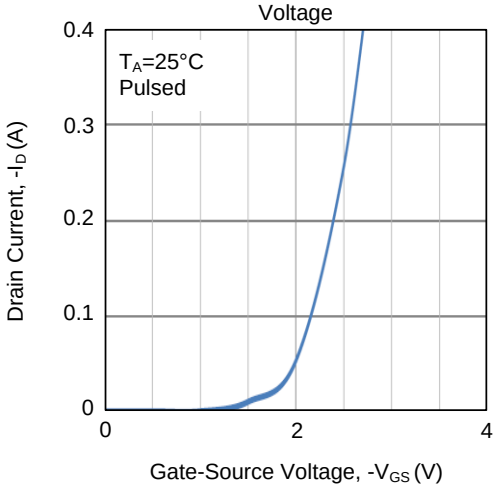
Gate Threshold Voltage vs. Junction Temperature



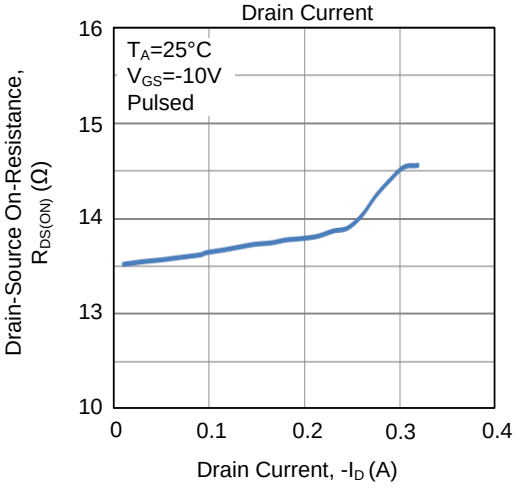
Source Current vs. Source-Drain Voltage



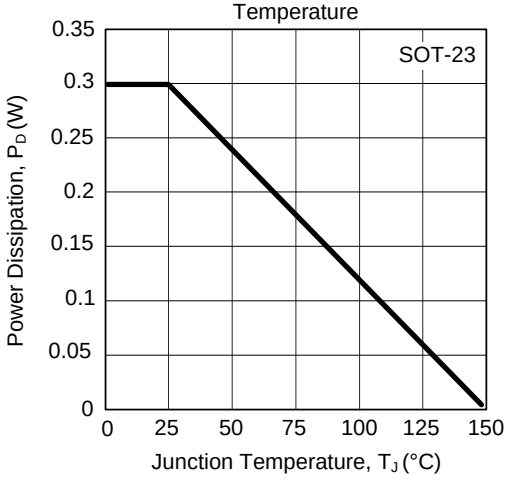
Drain Current vs. Gate-Source Voltage



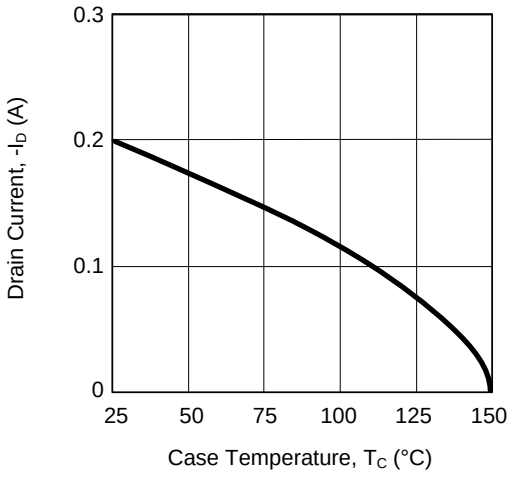
Drain-Source On-Resistance vs. Drain Current



Power Dissipation vs. Junction Temperature



Drain Current vs. Case Temperature



■ TYPICAL CHARACTERISTICS (Cont.)